



# Ruttonsha International Rectifier Ltd.

## THYRISTORS MODULE (NON ISOLATED TYPE)

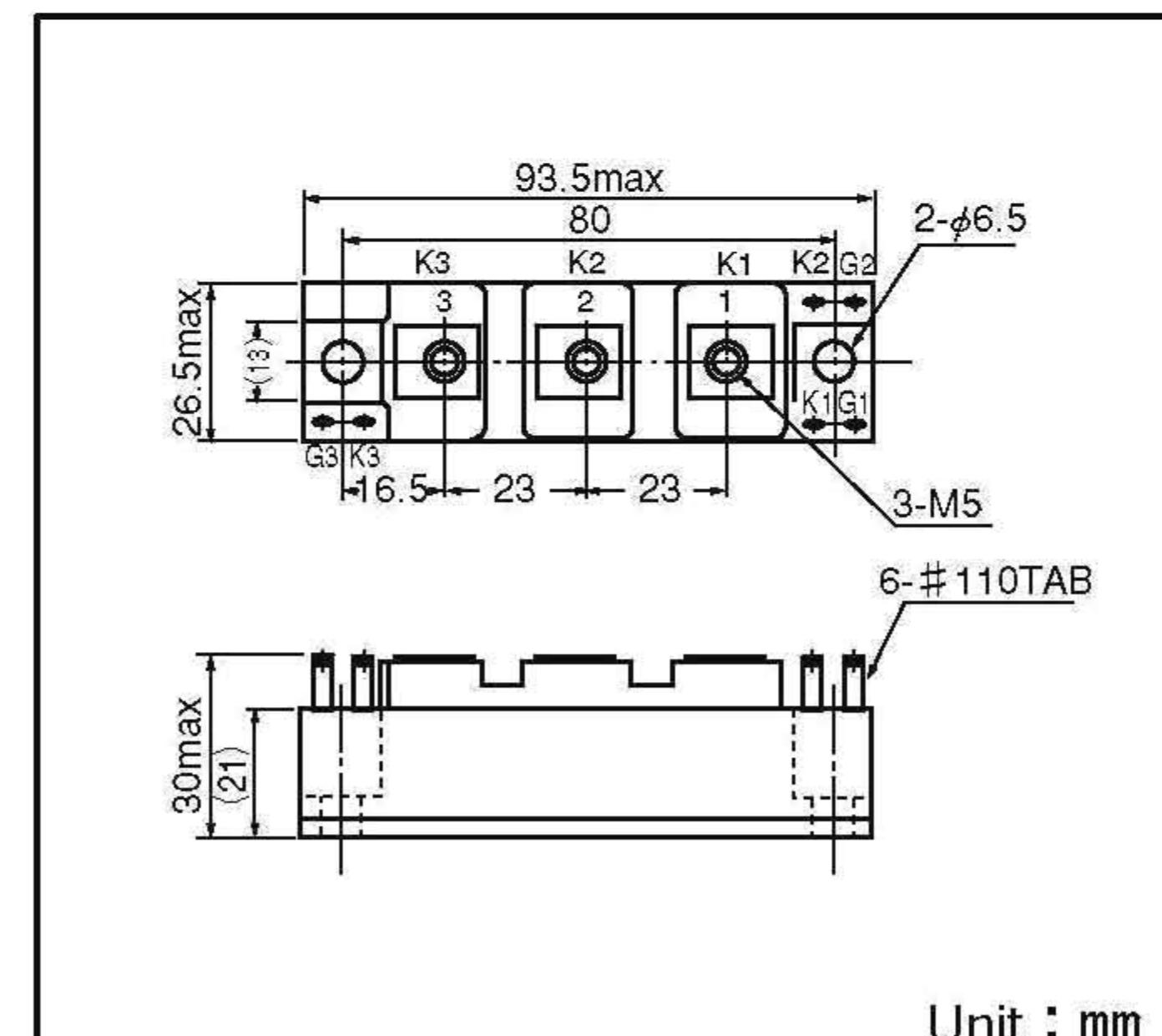
Type : RHTT 60 A 40

### Features

- $I_{T(AV)}$  60A (each device)
- High Surge Current 1640 A
- Easy Construction
- Non-isolated. Mounting base as common Anode terminal

### Applications

- Welding power Supply
- Various DC power Supply

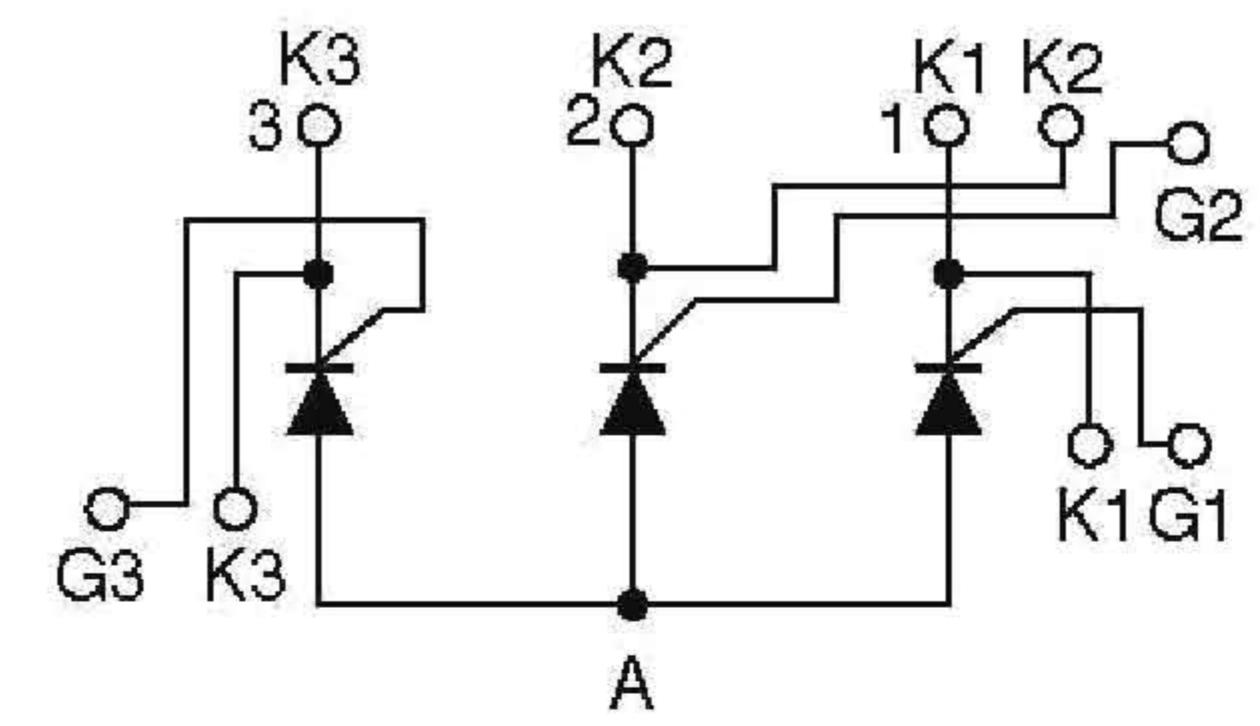


Unit : mm

### Major Ratings and Characteristics :-

PARAMETERS	RHTT 60 A 40	UNITS
$I_{T(AV)}$ or $I_{F(AV)}$ @ $T_c$	60 123	A $^{\circ}\text{C}$
$I_{T(RMS)}$ @ $T_c$	94 123	A $^{\circ}\text{C}$
$I_{TSM}$ @50Hz	1640	A
$I^2t$ @50Hz	13.5	KA <sup>2</sup> s
$V_{DRM}$ / $V_{RRM}$	400	V
$T_J$	- 30 to 150	$^{\circ}\text{C}$
$T_{STG}$	- 30 to 125	$^{\circ}\text{C}$

Circuit Diagram



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## ELECTRICAL SPECIFICATIONS

Type : RHTT 60 A

### Voltage Ratings

Type number	Voltage Code	$V_{DRM}/V_{RRM}$ , max repetitive peak and off-state voltage V	$V_{RSM}$ , maximum non-repetitive peak voltage V	$I_{DRM}/I_{RRM}$ max. @ $T_c = 125^\circ C$ mA
RHTT60 A 40	04	400	480	10

### On - state Conduction

Parameter	RHTT60 A 40	Units	Conditions
$I_{T(AV)}$ Max. average on-state current @ case temperature	60	A	Single phase, half wave, $180^\circ$ conduction
	123	$^\circ C$	
$I_{T(RMS)}$ Max RMS on-state current	94	A	Single phase, half wave, $180^\circ$ conduction, $T_c = 123^\circ C$
$I_{TSM}$ or $I_{FSM}$ Max. peak, half-cycle non-repetitive surge current	1640	A	$t = 10ms \ T_j = 25^\circ C$ No voltage reapplied
$I^2t$ Maximum $I^2t$ for fusing	13.5	$KA^2s$	$t = 10ms \ T_j = 25^\circ C$ No voltage reapplied
$V_{TM}$ Max peak on state voltage	1.25	V	180 A Peak $T_j = 25^\circ C$ $180^\circ$ conduction
$dv/dt$ Max. non-repetitive rate of rise of turned on current	50	$A/\mu s$	$I_G = 150mA, T_j = 25^\circ C, V_D = \frac{1}{2}V_{DRM},$ $dI_G/dt = 1A/\mu s$
$I_H$ Maximum holding current typ.	100	mA	$T_j = 25^\circ C$ , anode supply = 6V, resistive load, gate open circuit

### BLOCKING

$I_{RRM}$ Max. peak reverse and off-state leakage current at $V_{RRM}, V_{DRM}$	10	mA	$T_c = 125^\circ C$ , gate open circuit
$dv/dt$ Max. critical rate of rise of off-state Voltage	50	$V/\mu s$	$T_j = 125^\circ C$ linear to $0.67V_{DRM}$ , gate open circuit

### THERMAL AND MECHANICAL SPECIFICATIONS

$T_j$ Junction operating temperature range	- 30 to 150	$^\circ C$	
$T_{sg}$ Storage temp. range	- 30 to 125	$^\circ C$	
$R_{thJC}$ Max. internal thermal resistance, junction to case	0.35	$^\circ C/W$	$\frac{1}{3}$ module
T Mounting torque $\pm 10\%$ Module to heatsink	4.7	Nm	A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound.
	2.7	Nm	
Wt Approximate weight	170	g	

### ELECTRICAL SPECIFICATION

#### TRIGGERING

$V_{GT}$ Max. gate voltage required to trigger	2.0	V	$T_j = 25^\circ C$ , anode supply 6 V resistive load
$I_{GT}$ Max. gate current required to trigger	150	mA	
$P_{GM}$ Max. peak gate power	10	W	
$P_{G(AV)}$ Max. average gate power	1.0	W	
$I_{GM}$ Max. peak gate current	3.0	A	
$-V_{GM}$ Max. peak negative gate voltage	5.0	V	

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